

General Description

These N-channel enhanced vdmofets, is obtained by the self-aligned planar technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. Which accords with the RoHS standard.

Features

- Fast switching
- Low on-resistance
- Low gate charge and input capacitance
- 100% avalanche tested

Mechanical Data

- Case:TO-220,ITO-220,TO-263,TO-262,TO-251,TO-252 Package

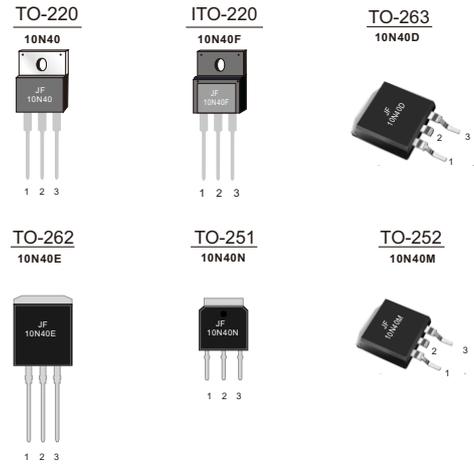
Application

- Switching applications

Ordering Information

Part No.	Package Type	Package	Quality(box)
10N40	TO-220	Tube	1000
10N40F	ITO-220	Tube	1000
10N40D	TO-263	Tape & Reel	800
10N40E	TO-262	Tube	1000
10N40N	TO-251	Tube	1000
10N40M	TO-252	Tape & Reel	3000

Product Summary			
V _{DS}	R _{DS(on)} (Ω) Typ	I _D (A)	Q _g (Typ)
400V	0.44 @ 10V	10	23nc



Block Diagram

Pin Definition:

1. Gate
2. Drain
3. Source

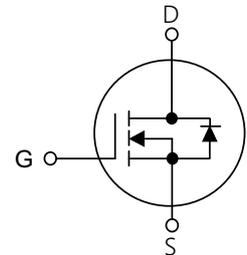


Table1 Absolute Maximum Ratings (T_C=25°C, unless otherwise specified)

Parameter	Symbol	10N40/10N40D/10N40E 10N40M/10N40N	10N40F	Unit
Drain-Source Voltage	V _{DS}	400		V
Gate-Source Voltage	V _{GS}	±30		V
Continuous Drain Current	I _D	T _C =25°C	10	A
		T _C =100°C	6.3	
Pulsed Drain Current (Note 1)	I _{DM}	40		A
Single Pulse Avalanche Energy(Note 2)	E _{AS}	450		mJ
Avalanche Current(Note 1)	I _{AR}	-		A
Power Dissipation T _C =25°C	P _D	100	35	W
Operating Junction and Storage Temperature	T _J /T _{STG}	-55~+175		°C

Table 2. Thermal Characteristics

Parameter	Symbol	10N40/10N40D/ 10N40M/10N40N 10N40E	10N40F	Unit
Thermal resistance Junction to Ambient	$R_{\theta JA}$	62.5	62.5	$^{\circ}\text{C}/\text{W}$
Thermal resistance Junction to Case	$R_{\theta JC}$	1.25	3.57	$^{\circ}\text{C}/\text{W}$

Table 3. Electrical Characteristics ($T_c=25^{\circ}\text{C}$, unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	400	-	-	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=400V, V_{GS}=0V$	-	-	1	μA
Gate- Source Leakage Current	Forward	$V_{GS}=30V, V_{DS}=0V$	-	-	100	nA
	Reverse	$V_{GS}=-30V, V_{DS}=0V$	-	-	-100	nA
On Characteristics(Note 4)						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.0	3.0	4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=5A$	-	0.44	0.55	Ω
Dynamic Characteristics(Note 5)						
Input Capacitance	C_{ISS}	$V_{DS}=25V, V_{GS}=0V, f=1\text{MHz}$	-	1126	-	pF
Output Capacitance	C_{OSS}		-	124	-	pF
Reverse Transfer Capacitance	C_{RSS}		-	8	-	pF
Switching Characteristics (Note 5)						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=200V, I_D=10A,$ $R_G=10\Omega$	-	18	-	ns
Turn-On Rise Time	t_R		-	23	-	ns
Turn-Off Delay Time	$t_{d(off)}$		-	41	-	ns
Turn-Off Fall Time	t_f		-	19	-	ns
Total Gate Charge	Q_G	$V_{DD}=320V, I_D=10A,$ $V_{GS}=10V$	-	23	-	nC
Gate-Source Charge	Q_{GS}		-	5.2	-	nC
Gate-Drain Charge	Q_{GD}		-	8.5	-	nC
Drain-Source Diode Characteristics and Maximum Ratings						
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=10A$	-	-	1.5	V
Maximum Continuous Drain-Source Diode Forward Current	I_S		-	-	10	A
Reverse Recovery Time	t_{rr}	$V_{GS}=0V, I_F=10A$	-	376	-	ns
Reverse Recovery Charge	Q_{RR}	$di_F/dt=100A/\mu s$ (Note 1)	-	2560	-	nC

Notes : 1 Repetitive Rating: Pulse width limited by maximum junction temperature

2 $L=10\text{mH}, I_D=9.5A, V_{DD}=50V, \text{Starting } T_J=25^{\circ}\text{C}$

4 Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$

5 Guaranteed by design, not subject to production

Typical Characteristics Diagrams

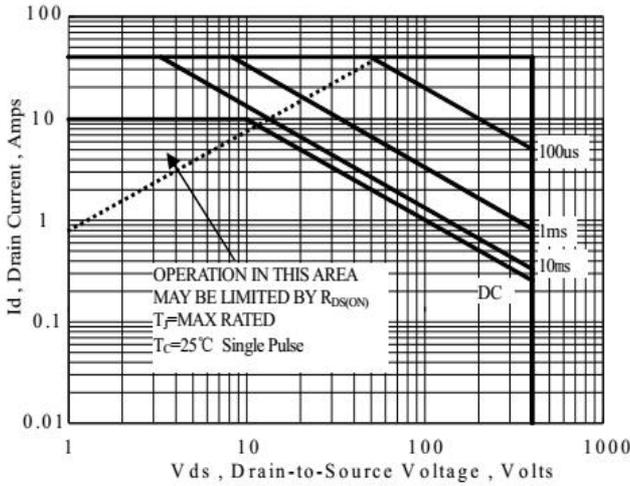


Figure 1 Maximum Forward Bias Safe Operating Area

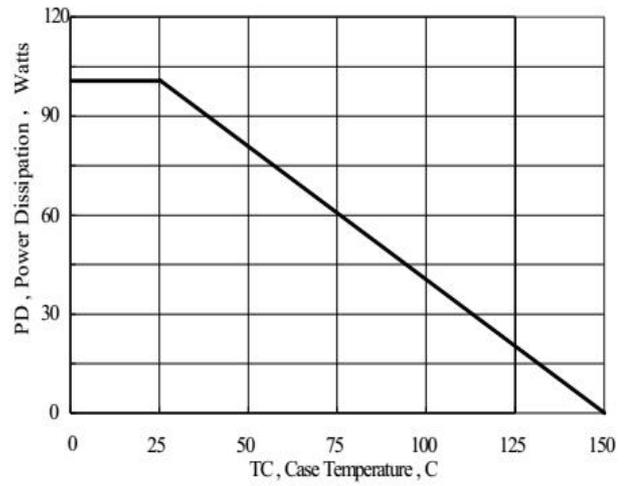


Figure 2 Maximum Power Dissipation vs Case Temperature

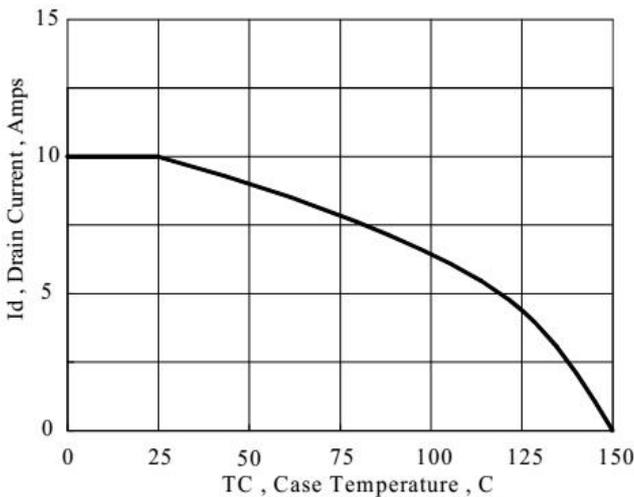


Figure 3 Maximum Continuous Drain Current vs Case Temperature

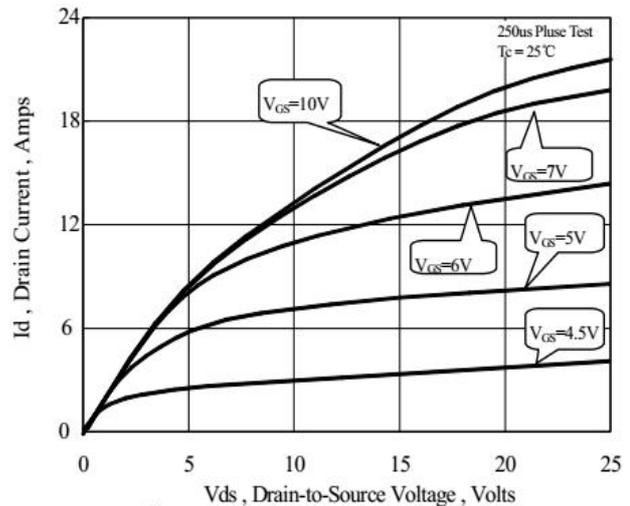


Figure 4 Typical Output Characteristics

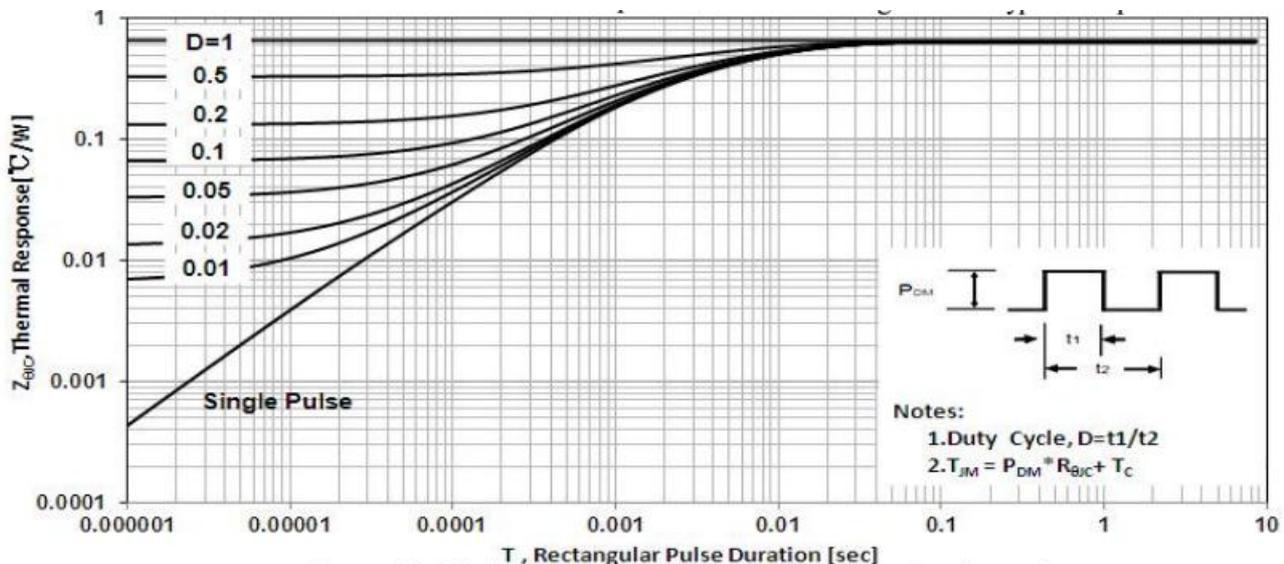


Figure 5 Maximum Effective Thermal Impedance, Junction to Case

Typical Characteristics Diagrams

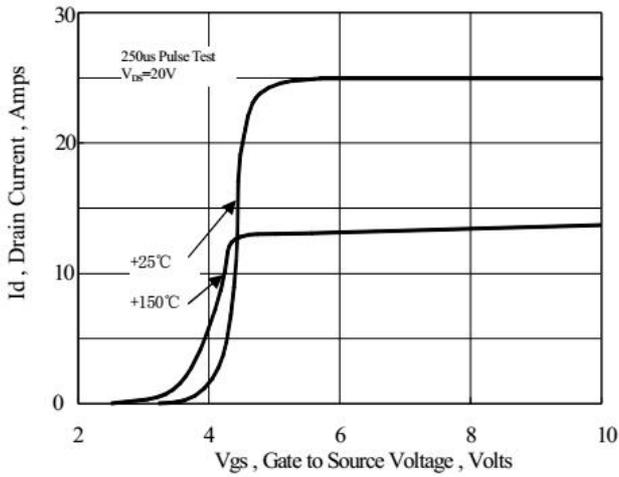


Figure 6 Typical Transfer Characteristics

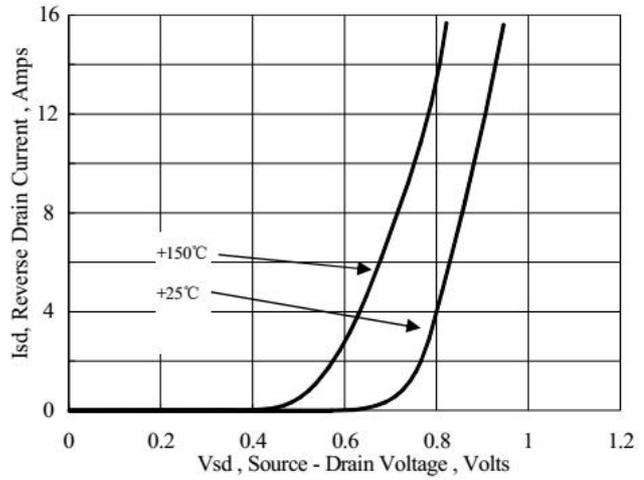


Figure 7 Typical Body Diode Transfer Characteristics

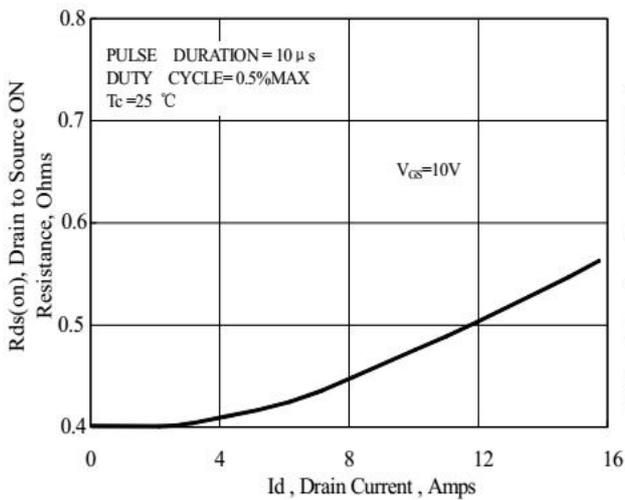


Figure 8 Typical Drain to Source ON Resistance vs Drain Current

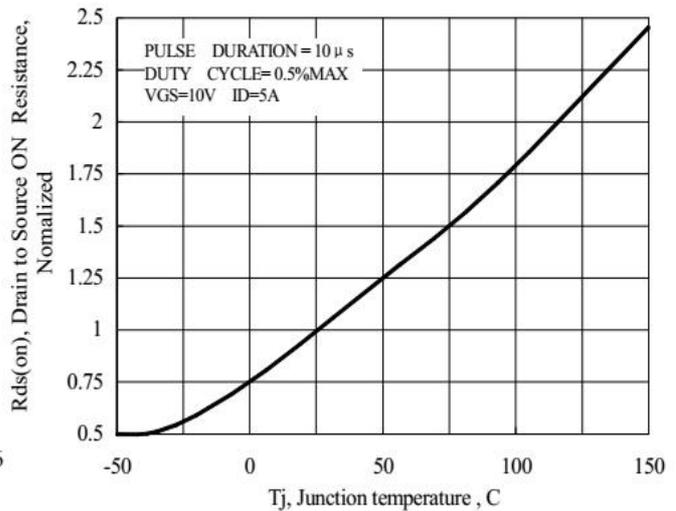


Figure 9 Typical Drain to Source on Resistance vs Junction Temperature

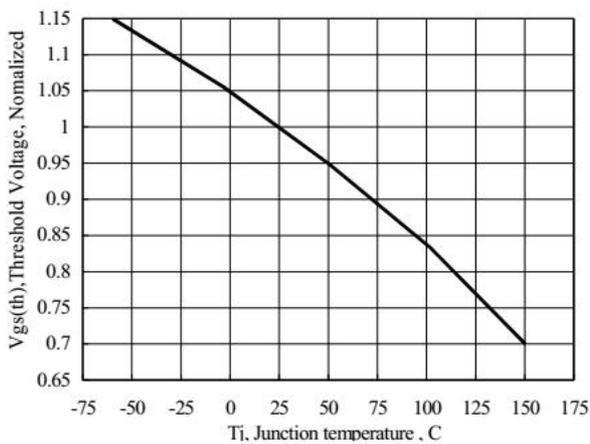


Figure 10 Typical Threshold Voltage vs Junction Temperature

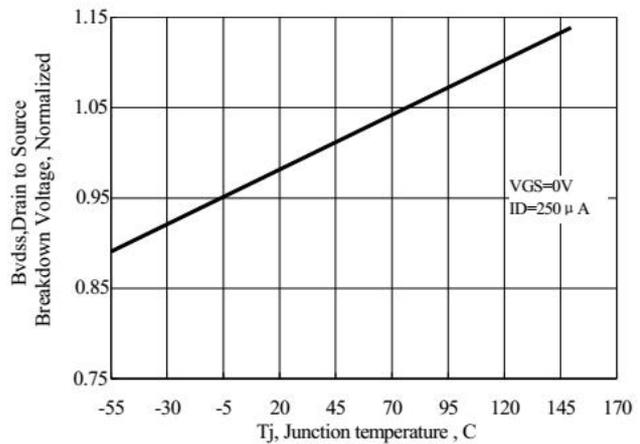


Figure 11 Typical Breakdown Voltage vs Junction Temperature

Typical Characteristics Diagrams

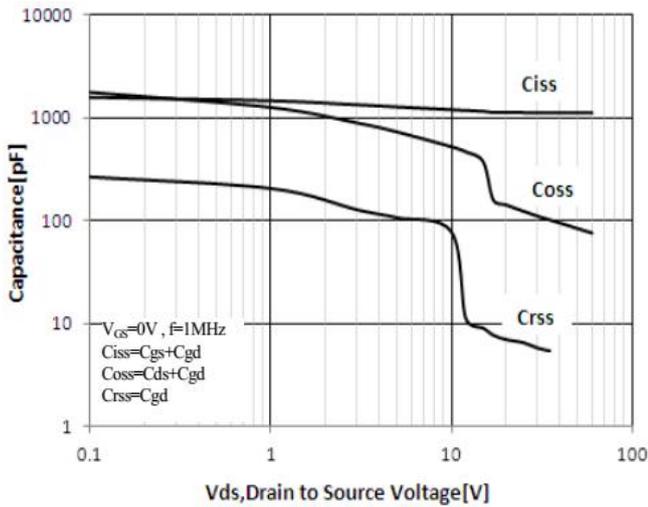


Figure 12 Typical Capacitance vs Drain to Source Voltage

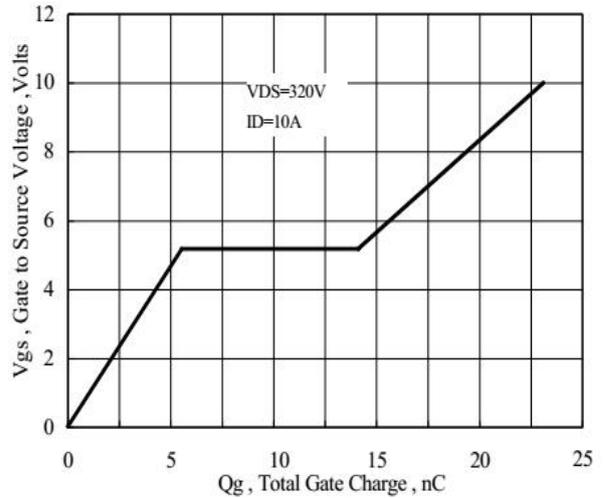


Figure 13 Typical Gate Charge vs Gate to Source Voltage

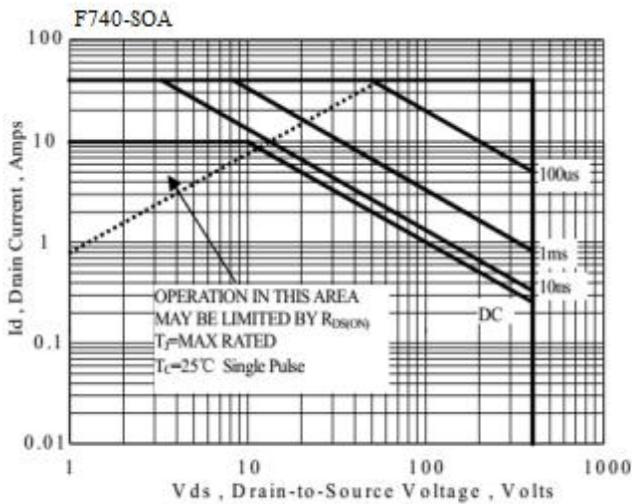


Figure 14 Maximum Forward Bias Safe Operating Area

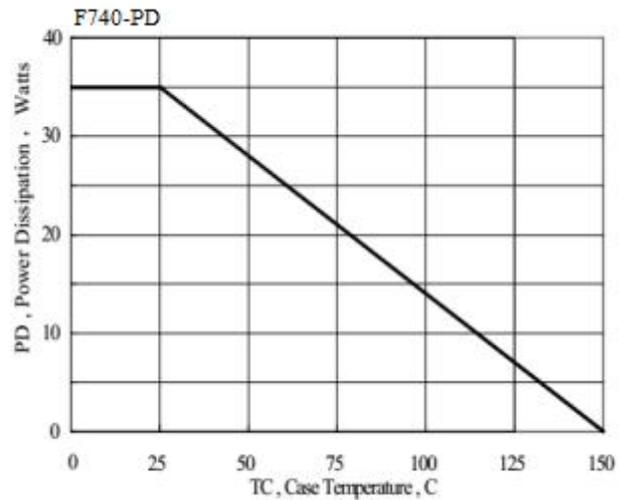


Figure 15 Maximum Power Dissipation vs Case Temperature

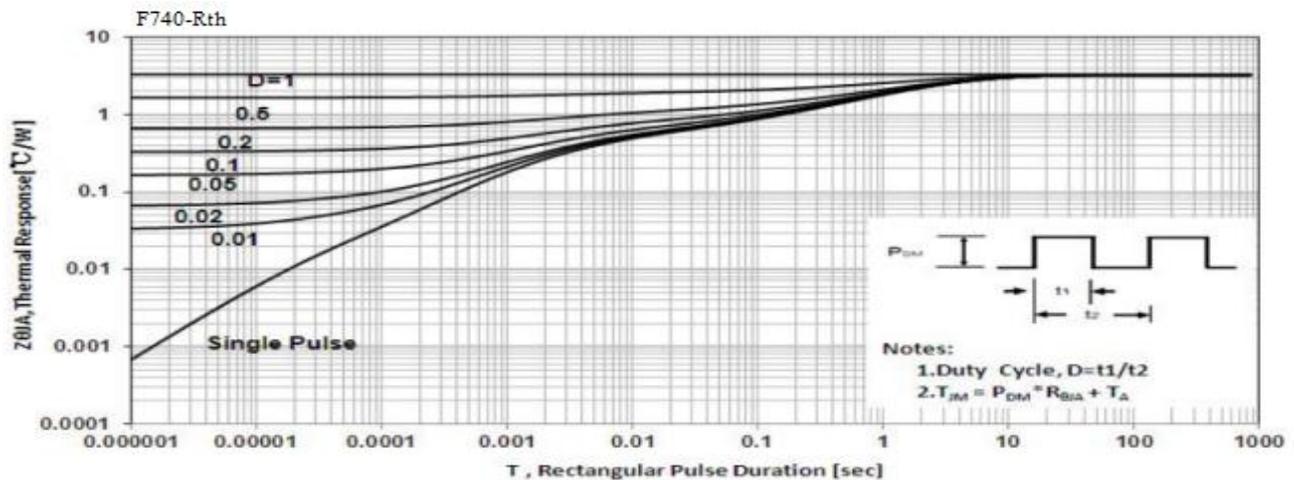
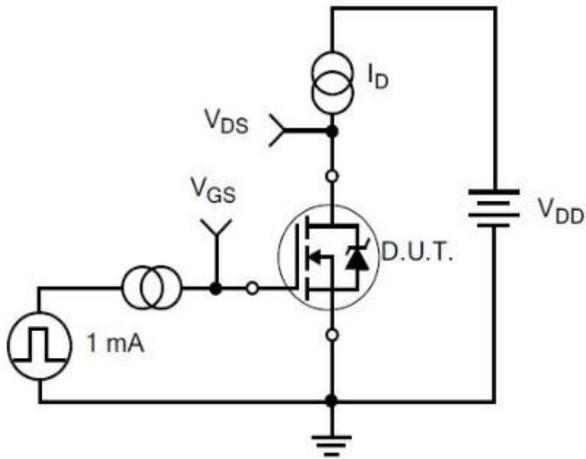
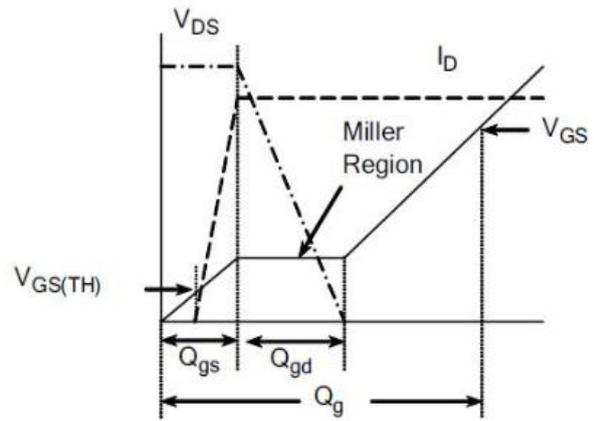


Figure 16 Maximum Effective Thermal Impedance, Junction to Case

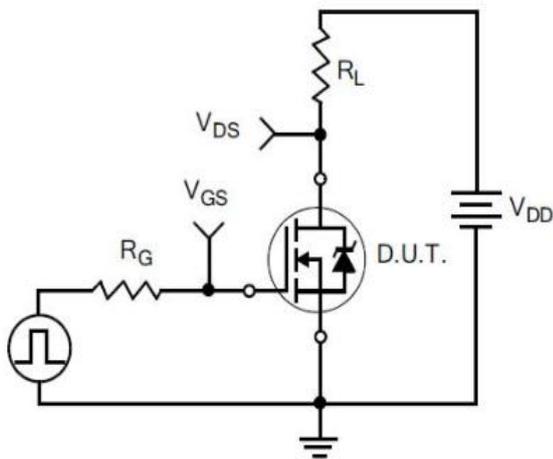
Typical Test Circuit



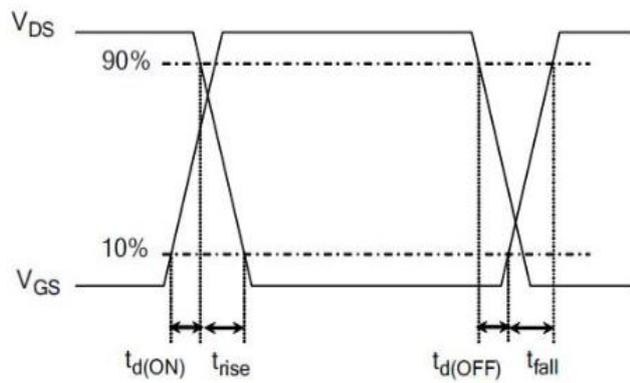
1) Gate Charge Test Circuit



2) Gate Charge Waveform

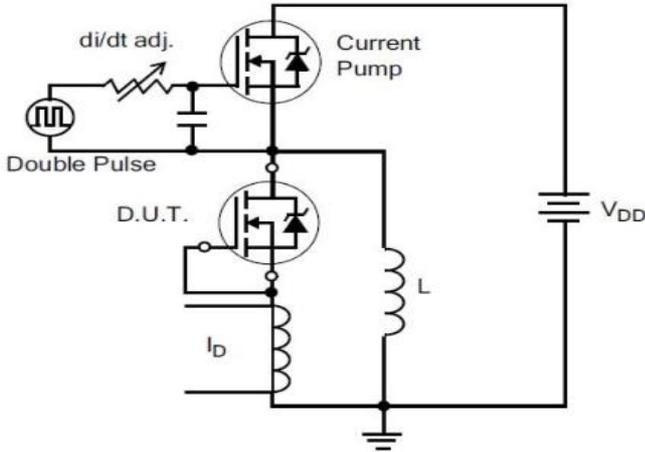


3) Resistive Switching Test Circuit

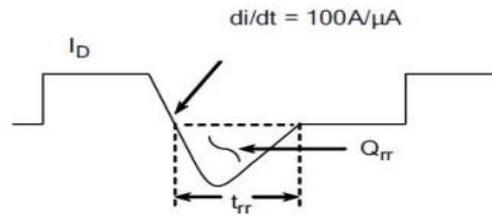


4) Resistive Switching Waveforms

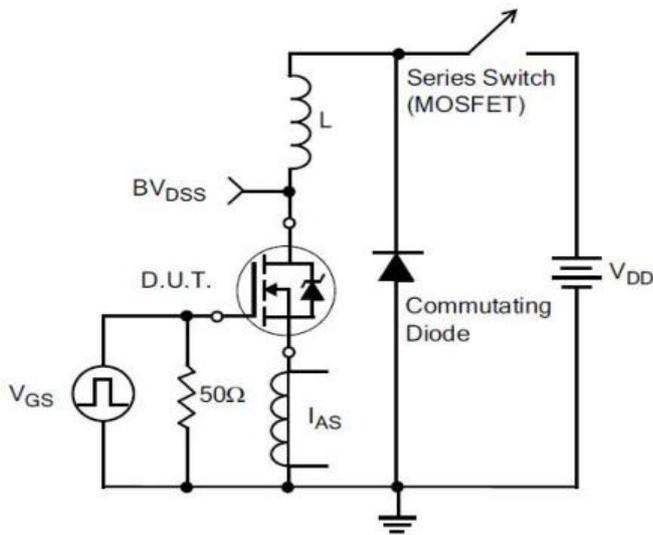
Typical Test Circuit



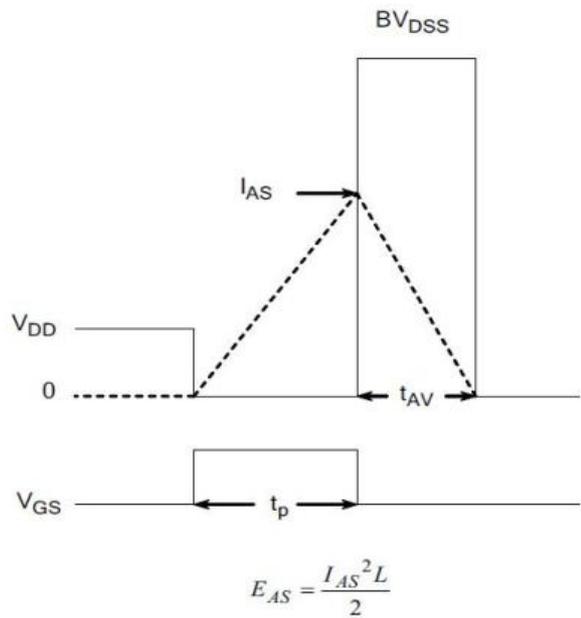
5) Diode Reverse Recovery Test Circuit



6) Diode Reverse Recovery Waveform

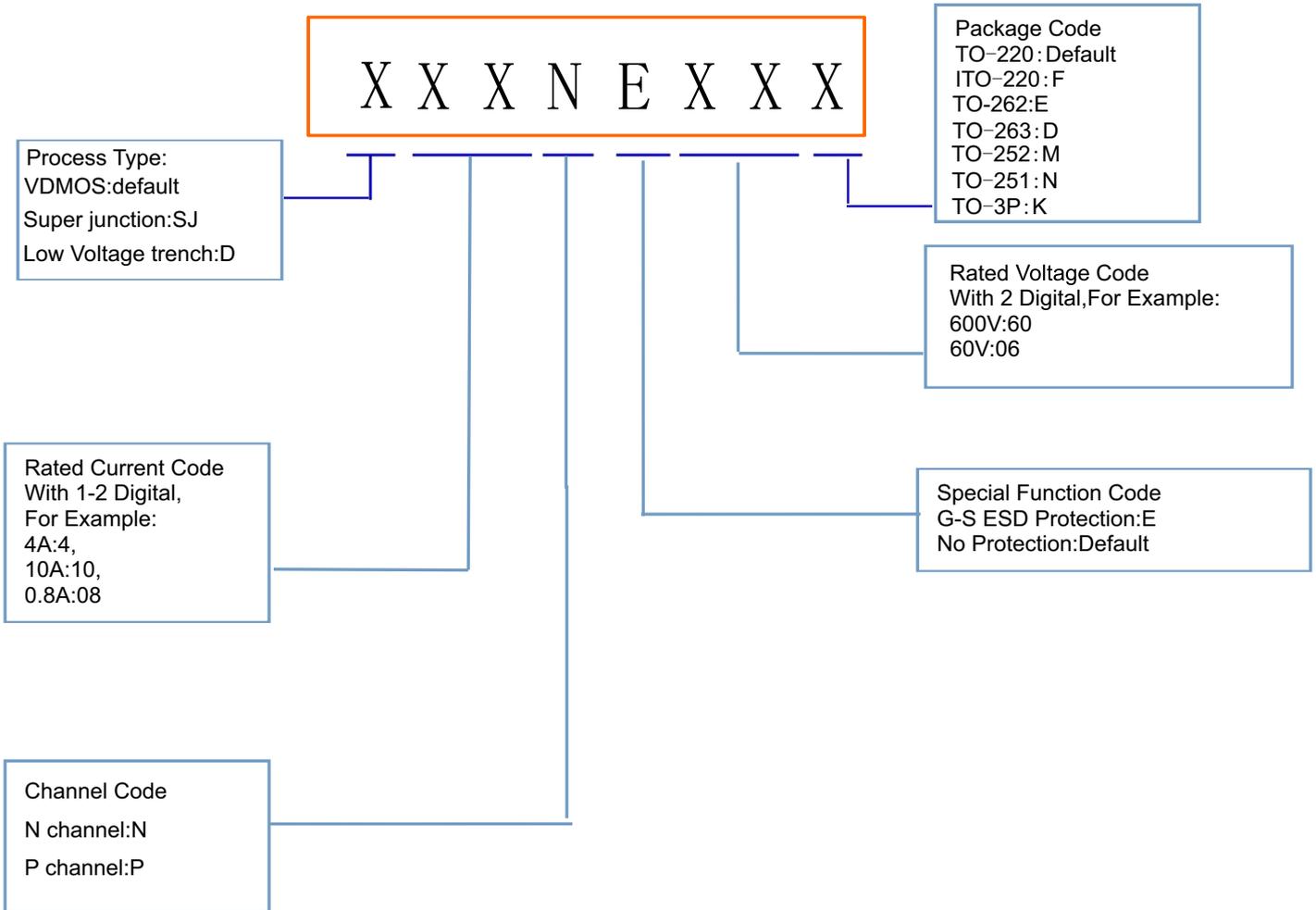


7) . Unclamped Inductive Switching Test Circuit



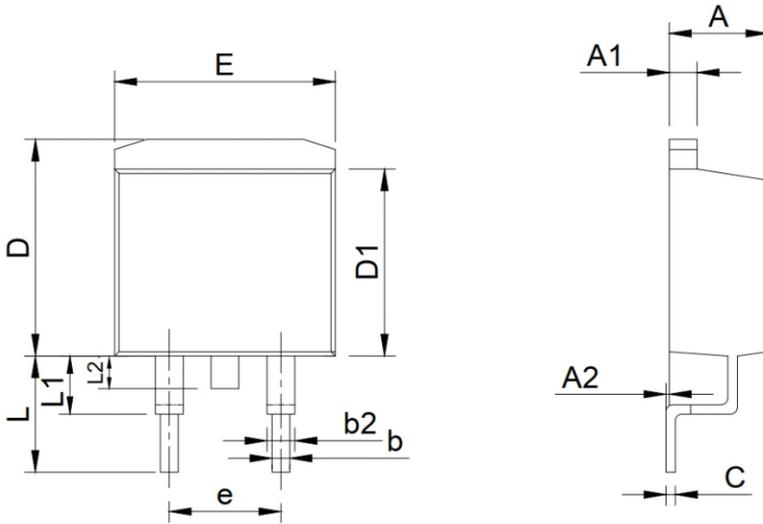
8) Unclamped Inductive Switching Waveforms

Product Names Rules



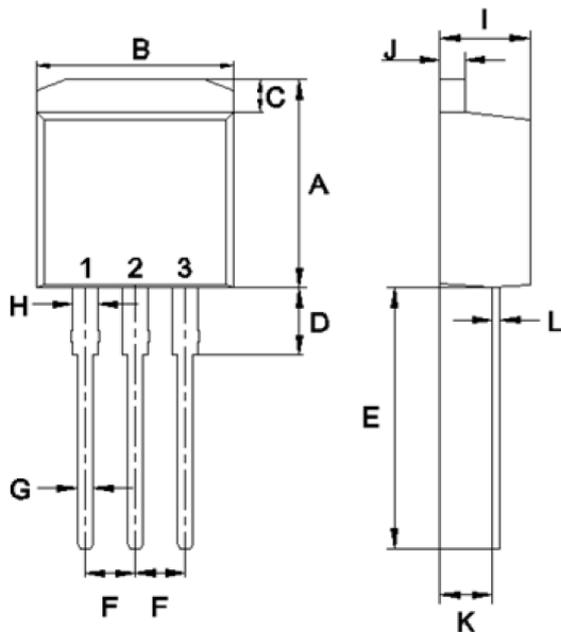
Dimensions

TO-263 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MIN	MAX	MIN	MAX
A	4.25	4.87	0.167	0.192
A1	1.07	1.47	0.042	0.058
A2	0	0.25	0.000	0.010
b	0.61	1.01	0.024	0.040
b1	1.2	1.34	0.047	0.053
C	0.3	0.6	0.012	0.024
D	9.48	10.84	0.373	0.427
D1	8.49	9.3	0.334	0.366
E	9.7	10.31	0.382	0.406
e	4.88	5.28	0.192	0.208
L	4.46	5.85	0.176	0.230
L1	1.33	2.33	0.052	0.092
L2	0	2.2	0.000	0.087

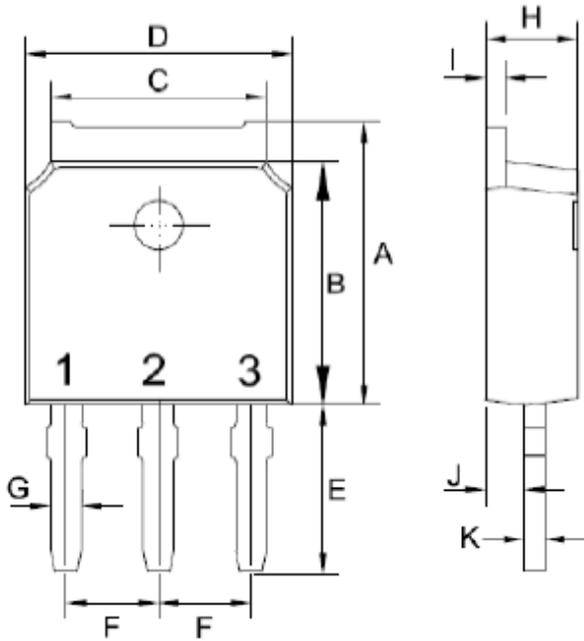
TO-262 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MIN	MAX	MIN	MAX
A	10.14	11.14	0.399	0.439
B	9.57	10.57	0.377	0.416
C	1.15	1.84	0.045	0.072
D	2.95	3.95	0.116	0.156
E	12.25	13.75	0.482	0.541
F	2.34	2.74	0.092	0.108
G	0.51	1.11	0.020	0.044
H	0.97	1.57	0.038	0.062
I	4.25	4.87	0.167	0.192
J	1.07	1.47	0.042	0.058
K	2.03	2.92	0.080	0.115
L	0.3	0.6	0.012	0.024

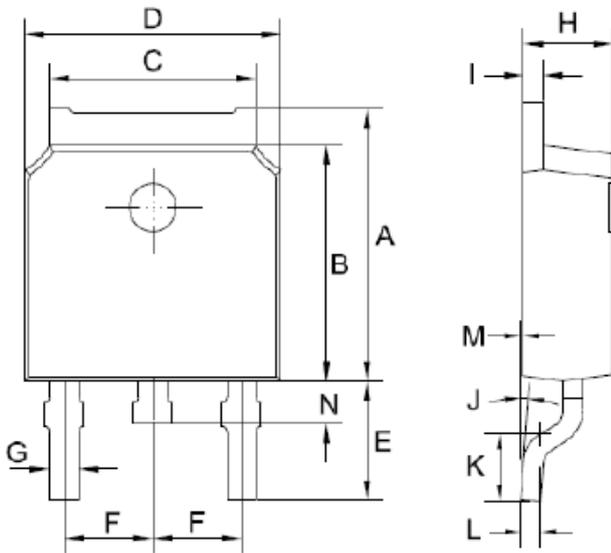
Dimensions

TO-251 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MIN	MAX	MIN	MAX
A	6.85	7.25	0.270	0.285
B	5.8	6.3	0.228	0.248
C	5	5.53	0.197	0.218
D	6.3	6.8	0.248	0.268
E	3.5	4.35	0.138	0.171
F	2.19	2.39	0.086	0.094
G	0.45	0.85	0.018	0.033
H	2.2	2.4	0.087	0.094
I	0.41	0.61	0.016	0.024
J	0.71	1.31	0.028	0.052
K	0.41	0.61	0.016	0.024

TO-252 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MIN	MAX	MIN	MAX
A	6.85	7.25	0.270	0.285
B	5.8	6.3	0.228	0.248
C	5	5.53	0.197	0.218
D	6.3	6.8	0.248	0.268
E	2.6	3.3	0.102	0.130
F	2.19	2.39	0.086	0.094
G	0.45	0.85	0.018	0.033
H	2.2	2.4	0.087	0.094
I	0.41	0.61	0.016	0.024
J	0.71	1.31	0.028	0.052
K	1.45	1.85	0.057	0.073
L	0.41	0.61	0.016	0.024
M	0	0.12	0.000	0.005
P	0.6	1	0.024	0.039

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